

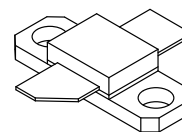
The RF Line
NPN Silicon
RF Power Transistor

MRF16006

6.0 WATTS, 1.6 GHz
RF POWER TRANSISTOR
NPN SILICON

Designed for 28 Volt microwave large-signal, common base, Class-C CW amplifier applications in the range 1600 – 1640 MHz.

- Specified 28 Volt, 1.6 GHz Class-C Characteristics
Output Power = 6 Watts
Minimum Gain = 7.4 dB, @ 6 Watts
Minimum Efficiency = 40% @ 6 Watts
- Characterized with Series Equivalent Large-Signal Parameters from 1500 MHz to 1700 MHz
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.



CASE 395C-01, STYLE 2

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	60	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector-Current	I_C	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	26 0.15	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

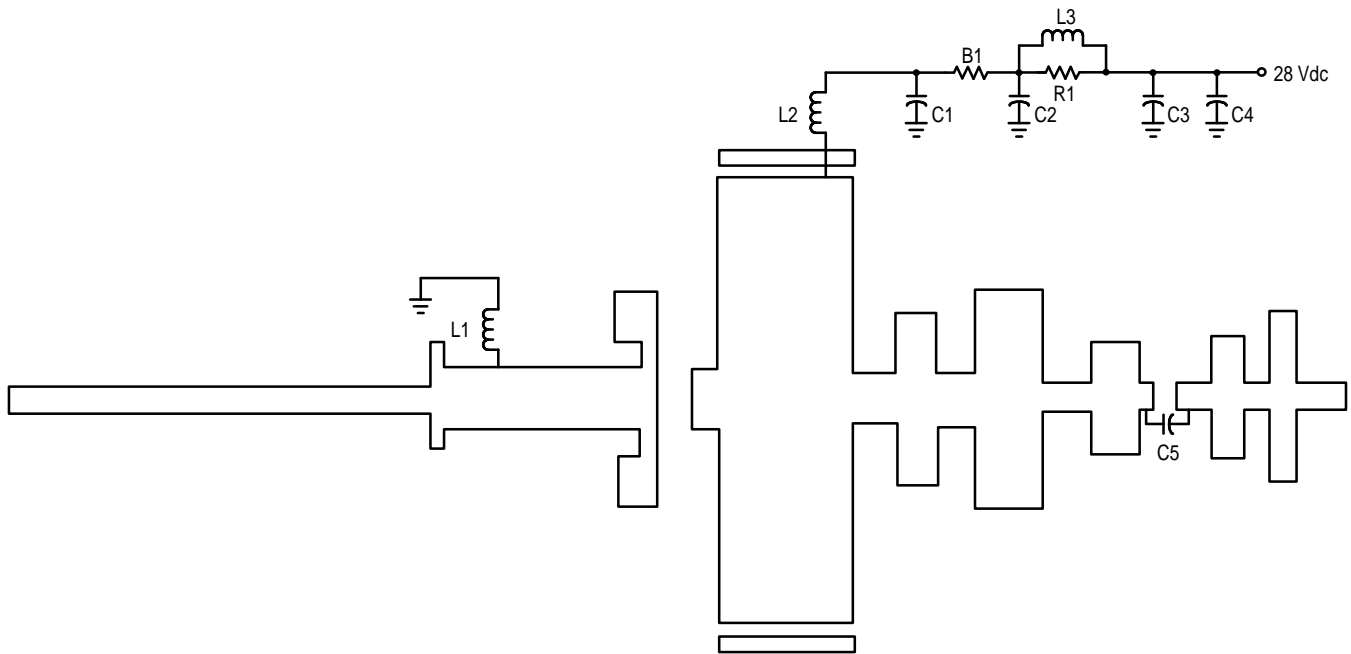
Thermal Resistance — Junction to Case (1) (2)	$R_{\theta JC}$	6.8	$^\circ\text{C/W}$
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(1) Thermal measurement performed using CW RF operating condition.

(2) Thermal resistance is determined under specified RF operating conditions by infrared measurement techniques.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

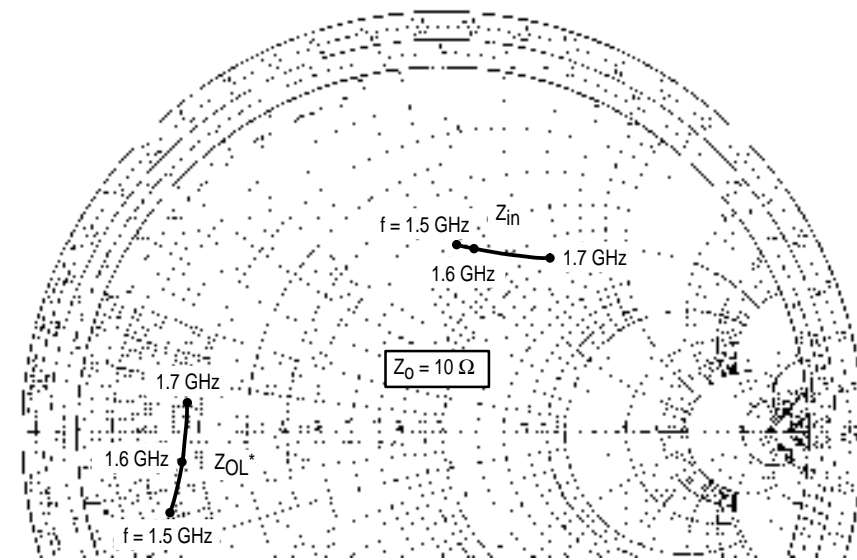
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 40\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	55	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 40\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	55	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 2.5\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 28\text{ Vdc}$, $V_{BE} = 0$)	I_{CES}	—	—	2.5	mAdc
ON CHARACTERISTICS					
DC Current Gain ($I_{CE} = 0.2\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	20	—	80	—
DYNAMIC CHARACTERISTICS					
Output Capacitance ($V_{CB} = 28\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{ob}	11	—	—	pf
FUNCTIONAL TESTS					
Common–Base Amplifier Power Gain ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 6\text{ Watts}$, $f = 1600/1640\text{ MHz}$)	G_{pe}	7.4	—	—	dB
Collector Efficiency ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 6\text{ Watts}$, $f = 1600/1640\text{ MHz}$)	η	40	45	—	%
Return Loss ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 6\text{ Watts}$, $f = 1600/1640\text{ MHz}$)	I_{RL}	—	8.0	—	dB
Output Mismatch Stress ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 6\text{ Watts}$, $f = 1600\text{ MHz}$, Load VSWR = 3:1 all phase angles at frequency of test)	ψ	No Degradation in Output Power			



Board Material – Teflon® Glass Laminate Dielectric
 Thickness – 0.30", $\epsilon_r = 2.55$ ", 2.0 oz. Copper

- | | | | |
|--------|------------------------------|--------|--------------------------------------|
| B1 | Fair Rite Bead on #24 Wire | C4 | 47 μ F, 50 V, Electrolytic Cap |
| C1, C5 | 100 pF, B Case, ATC Chip Cap | L1, L2 | 3 Turns, #18, 0.133" ID, 0.15" Long |
| C2 | 0.1 μ F, Dipped Mica Cap | L3 | 9 Turns, #24 Enamel |
| C3 | 0.1 μ F, Chip Cap | R1 | 82 Ω , 1.0 W, Carbon Resistor |

Figure 1. MRF16006 Test Fixture Schematic



$V_{CC} = 28$ Vdc, $P_{out} = 6$ W

f MHz	Z_{in} Ohms	Z_{OL}^* Ohms
1500	6.28 + j 8.53	1.22 - j 1.37
1600	7.04 + j 9.00	1.58 - j 0.53
1700	9.55 + j 12.86	1.71 + j 0.39

Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 2. Series Equivalent Input/Output Impedance

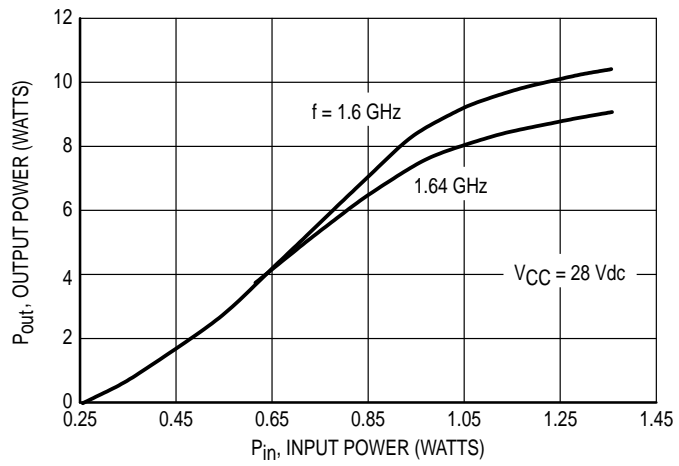
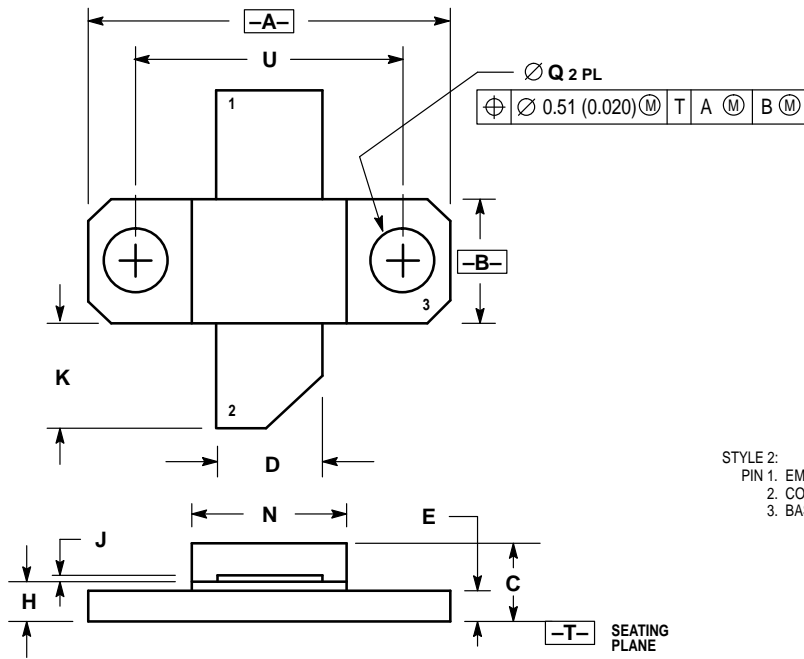


Figure 3. Output Power versus Input Power

PACKAGE DIMENSIONS




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.739	0.750	18.77	19.05
B	0.240	0.260	6.10	6.60
C	0.165	0.198	4.19	5.03
D	0.215	0.225	5.46	5.72
E	0.055	0.070	1.40	1.78
H	0.079	0.091	2.01	2.31
J	0.004	0.006	0.10	0.15
K	0.210	0.240	5.33	6.10
N	0.315	0.330	8.00	8.38
Q	0.125	0.135	3.18	3.42
U	0.560 BSC		14.23 BSC	

- STYLE 2:
 PIN 1. EMITTER
 2. COLLECTOR
 3. BASE

**CASE 395C-01
 ISSUE A**

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MRF16006/D

